Today

- Storage technologies and trends
- Locality of reference
- Caching in the memory hierarchy

Random-Access Memory (RAM)

Key features

- RAM is traditionally packaged as a chip.
- Basic storage unit is normally a cell (one bit per cell).
- Multiple RAM chips form a memory.

RAM comes in two varieties:

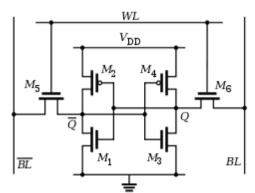
- SRAM (Static RAM)
- DRAM (Dynamic RAM)

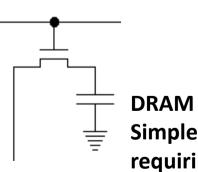
SRAM vs DRAM Summary

| | Trans. per bit | Access time | Needs refresh? | Needs EDC*? | Cost | Applications |
|------|-------------------|-------------|----------------|----------------|------|------------------------------|
| SRAM | 4 or 6 | 1x | No | Maybe | 100x | Cache memories |
| DRAM | 1 | 10x | Yes | Yes | 1x | Main memories, frame buffers |

^{*}EDC: Error detection and correction

SRAM
6 transistors /
bitcell costs a lot!





but cap drains.

Simple, but cap drains, requiring refresh

1GB SRAM: \$5000

1GB DRAM: \$20-\$75

Enhanced DRAMs

- Basic DRAM cell has not changed since its invention in 1966.
 - Commercialized by Intel in 1970.
- DRAM cores with better interface logic and faster I/O :
 - Synchronous DRAM (SDRAM)
 - Uses a conventional clock signal instead of asynchronous control
 - Double data-rate synchronous DRAM (DDR SDRAM)
 - Double edge clocking sends two bits per cycle per pin
 - Different types distinguished by size of small prefetch buffer:
 - DDR (2 bits), DDR2 (4 bits), DDR3 (8 bits), DDR4 (16 bits)
 - By 2010, standard for most server and desktop systems
 - Intel Core i7 supports DDR3 and DDR4 SDRAM

Nonvolatile Memories

- DRAM and SRAM are volatile memories
 - Lose information if powered off.
- Nonvolatile memories retain value even if powered off
 - Read-only memory (ROM): programmed during production
 - Programmable ROM (PROM): can be programmed once
 - Eraseable PROM (EPROM): can be bulk erased (UV, X-Ray)
 - Electrically eraseable PROM (EEPROM): electronic erase capability
 - Flash memory: EEPROMs, with partial (block-level) erase capability
 - Wears out after about 100,000 erasings
 - Ferro-electric RAM (FRAM), Resistive RAM
 - 3D XPoint (Intel Optane) & emerging NVMs
 - New materials

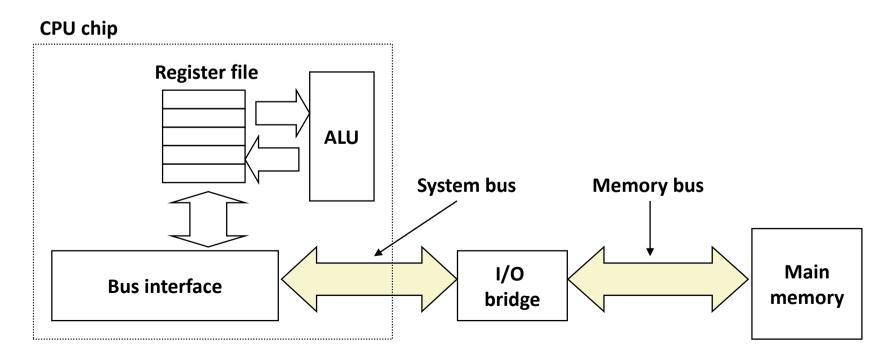


Uses for Nonvolatile Memories

- Firmware programs stored in a ROM (BIOS, controllers for disks, network cards, graphics accelerators, security subsystems,...)
- Solid state disks (replace rotating disks in thumb drives, smart phones, mp3 players, tablets, laptops, data centers,...)
- Disk caches

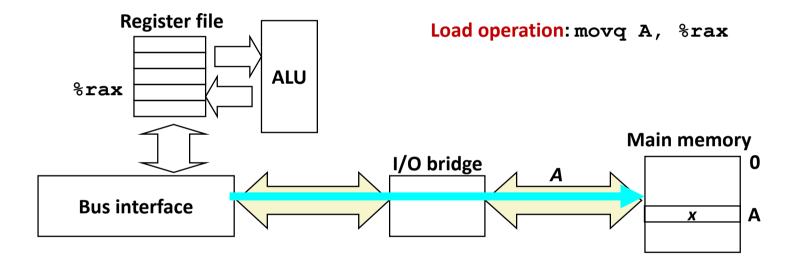
Traditional Bus Structure Connecting CPU and Memory

- A bus is a collection of parallel wires that carry address, data, and control signals.
- Buses are typically shared by multiple devices.



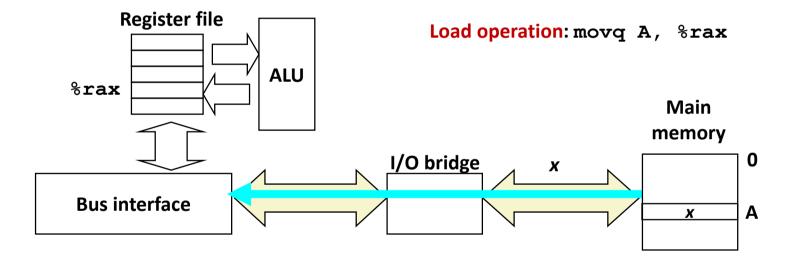
Memory Read Transaction (1)

■ CPU places address A on the memory bus.



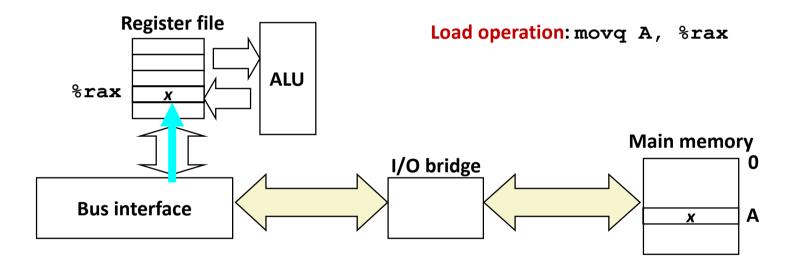
Memory Read Transaction (2)

Main memory reads A from the memory bus, retrieves word x, and places it on the bus.



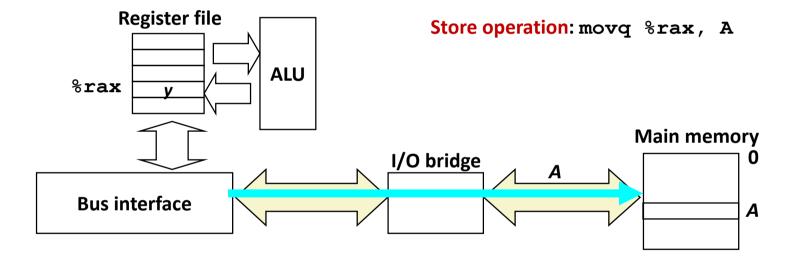
Memory Read Transaction (3)

CPU read word x from the bus and copies it into register %rax.



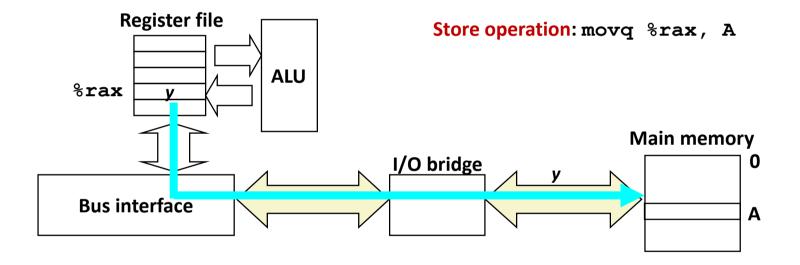
Memory Write Transaction (1)

CPU places address A on bus. Main memory reads it and waits for the corresponding data word to arrive.



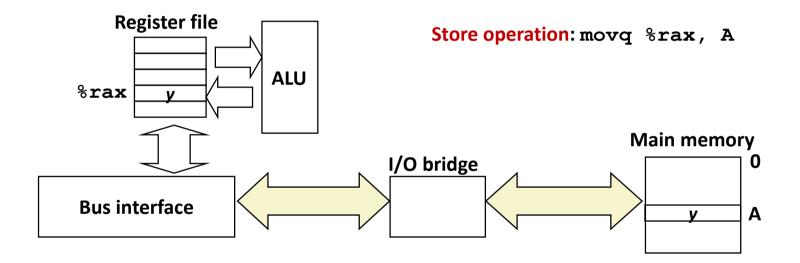
Memory Write Transaction (2)

CPU places data word y on the bus.

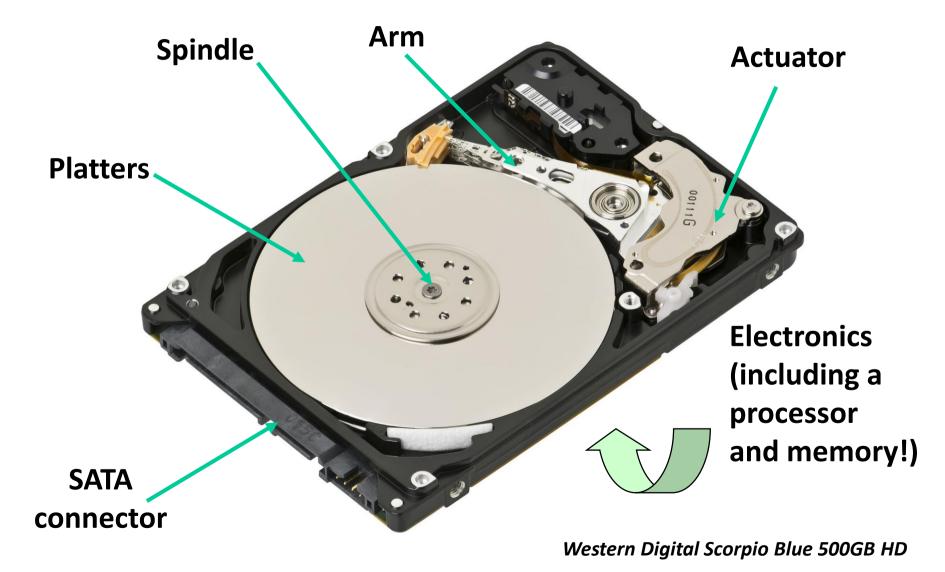


Memory Write Transaction (3)

Main memory reads data word y from the bus and stores it at address A.

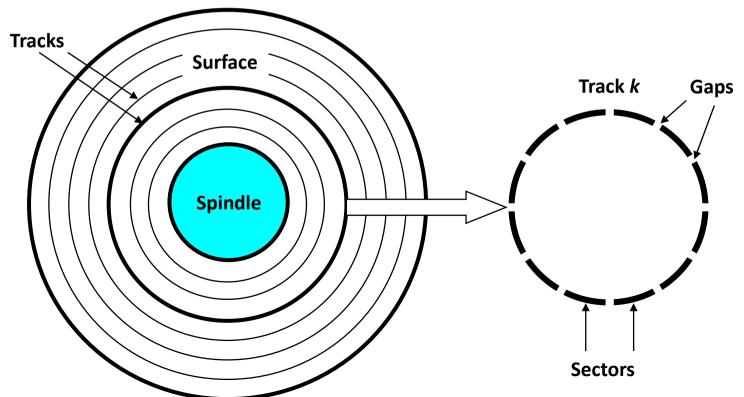


What's Inside A Disk Drive?



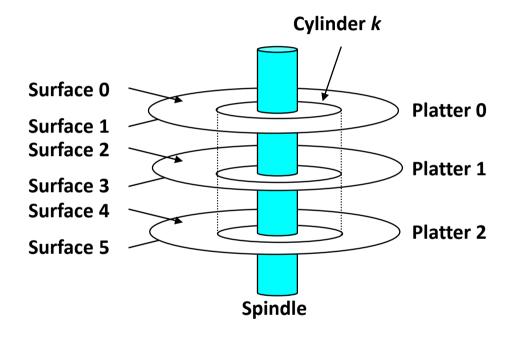
Disk Geometry

- Disks consist of platters, each with two surfaces.
- Each surface consists of concentric rings called tracks.
- Each track consists of sectors separated by gaps.



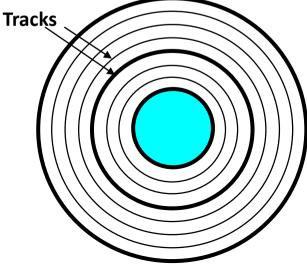
Disk Geometry (Multiple-Platter View)

Aligned tracks form a cylinder.



Disk Capacity

- Capacity: maximum number of bits that can be stored.
 - Vendors express capacity in units of gigabytes (GB) or terabytes (TB), where 1 GB = 10^9 Bytes and 1 TB = 10^{12} Bytes
- Capacity is determined by these technology factors:
 - Recording density (bits/in): number of bits that can be squeezed into a 1 inch segment of a track.
 - Track density (tracks/in): number of tracks that can be squeezed into a 1 inch radial segment.
 - Areal density (bits/in²): product of recording and track density.



Computing Disk Capacity

```
Capacity = (# bytes/sector) x (avg. # sectors/track) x (# tracks/surface) x (# surfaces/platter) x (# platters/disk)
```

Example:

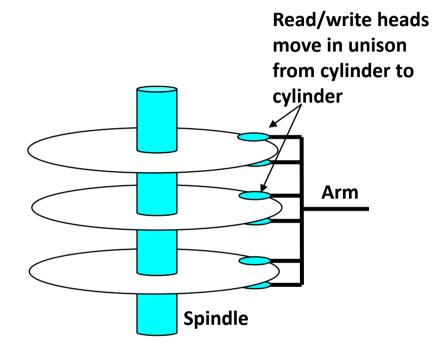
- 512 bytes/sector
- 300 sectors/track (on average)
- 20,000 tracks/surface
- 2 surfaces/platter
- 5 platters/disk

```
Capacity = 512 x 300 x 20,000 x 2 x 5
= 30,720,000,000
= 30.72 GB
```

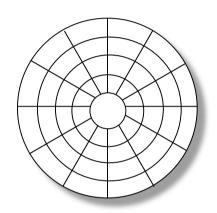
Disk Operation (Single-Platter View)

The disk surface The read/write head spins at a fixed is attached to the end rotational rate of the arm and flies over the disk surface on a thin cushion of air. spindle By moving radially, the arm can position the read/write head over any track.

Disk Operation (Multi-Platter View)



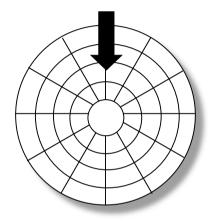
Disk Structure - top view of single platter



Surface organized into tracks

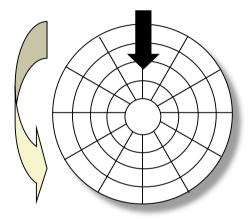
Tracks divided into sectors

Disk Access



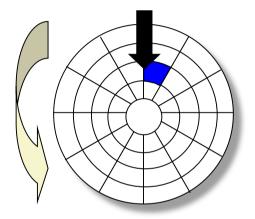
Head in position above a track

Disk Access



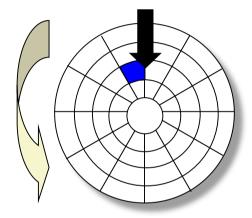
Rotation is counter-clockwise

Disk Access – Read



About to read blue sector

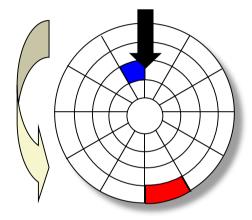
Disk Access - Read



After **BLUE** read

After reading blue sector

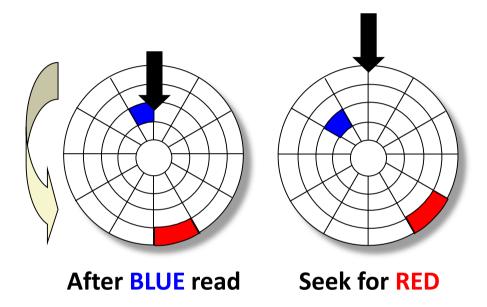
Disk Access - Read



After BLUE read

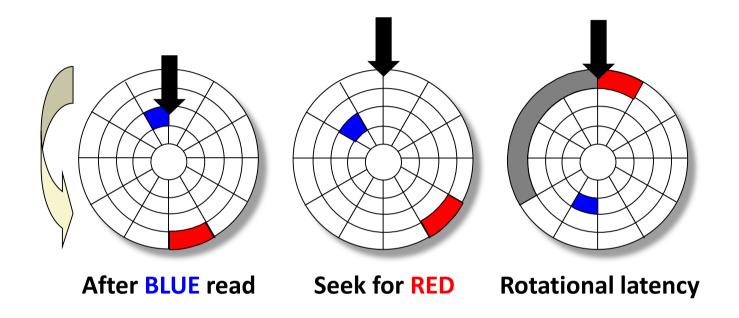
Red request scheduled next

Disk Access – Seek



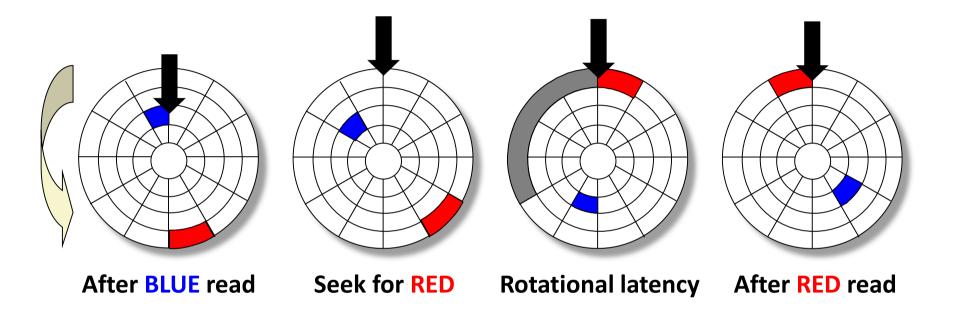
Seek to red's track

Disk Access – Rotational Latency



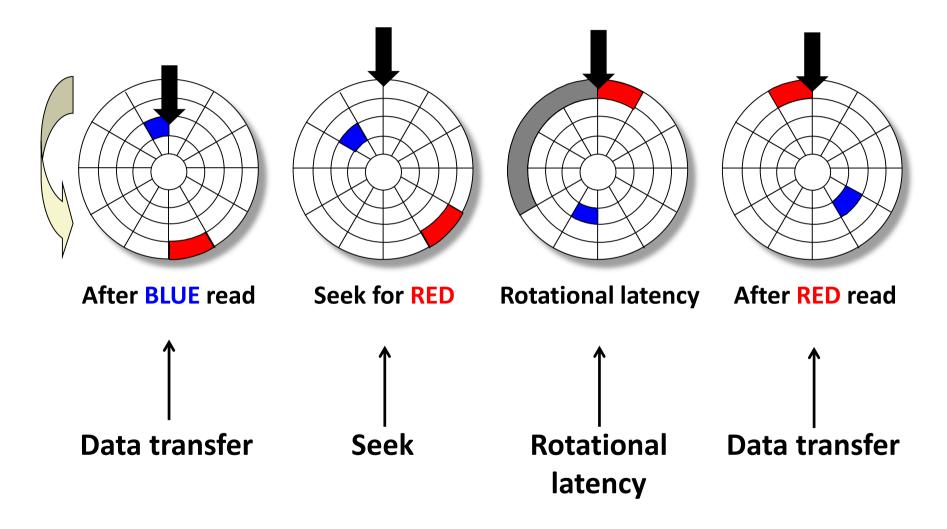
Wait for red sector to rotate around

Disk Access - Read



Complete read of red

Disk Access – Service Time Components



Disk Access Time

Average time to access some target sector approximated by:

- $T_{access} = T_{avg seek} + T_{avg rotation} + T_{avg transfer}$
- Seek time (T_{avg seek})
 - Time to position heads over cylinder containing target sector.
 - Typical T_{avg seek} is 3—9 ms
- Rotational latency (T_{avg rotation})
 - Time waiting for first bit of target sector to pass under r/w head.
 - $T_{avg rotation} = 1/2 \times 1/RPMs \times 60 sec/1 min$
 - Typical RPM = 7,200 RPMs
- Transfer time (T_{avg transfer})
 - Time to read the bits in the target sector.
 - $T_{avg transfer} = 1/RPM \times 1/(avg # sectors/track) \times 60 secs/1 min.$

Disk Access Time Example

Given:

- Rotational rate = 7,200 RPM
- Average seek time = 9 ms.
- Avg # sectors/track = 400.

Derived:

- $T_{avg\ rotation} = 1/2\ x\ (60\ secs/7200\ RPM)\ x\ 1000\ ms/sec = 4\ ms$.
- $T_{avg transfer} = 60/7200 \text{ RPM x } 1/400 \text{ secs/track x } 1000 \text{ ms/sec} = 0.02 \text{ ms}$
- $T_{access} = 9 \text{ ms} + 4 \text{ ms} + 0.02 \text{ ms}$

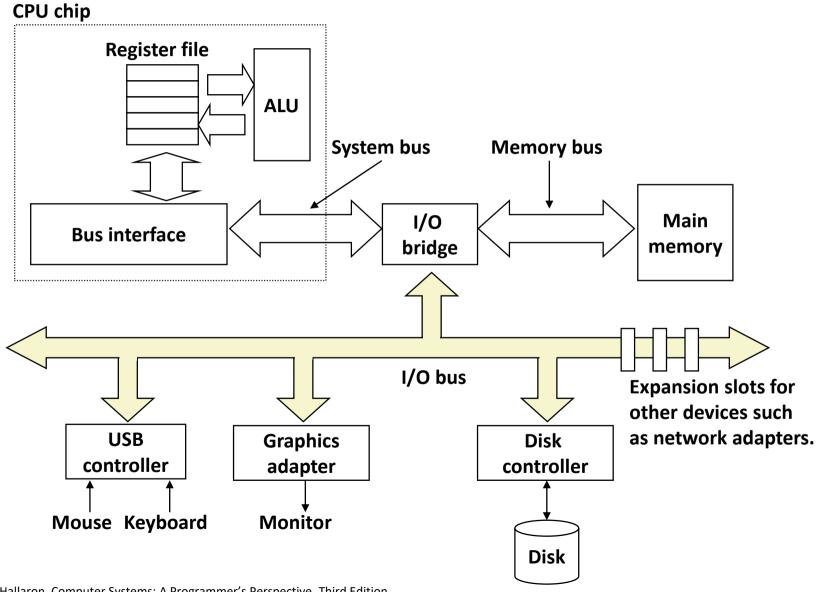
Important points:

- Access time dominated by seek time and rotational latency.
- First bit in a sector is the most expensive, the rest are free.
- SRAM access time is about 4 ns/doubleword, DRAM about 60 ns
 - Disk is about 40,000 times slower than SRAM,
 - 2,500 times slower then DRAM.

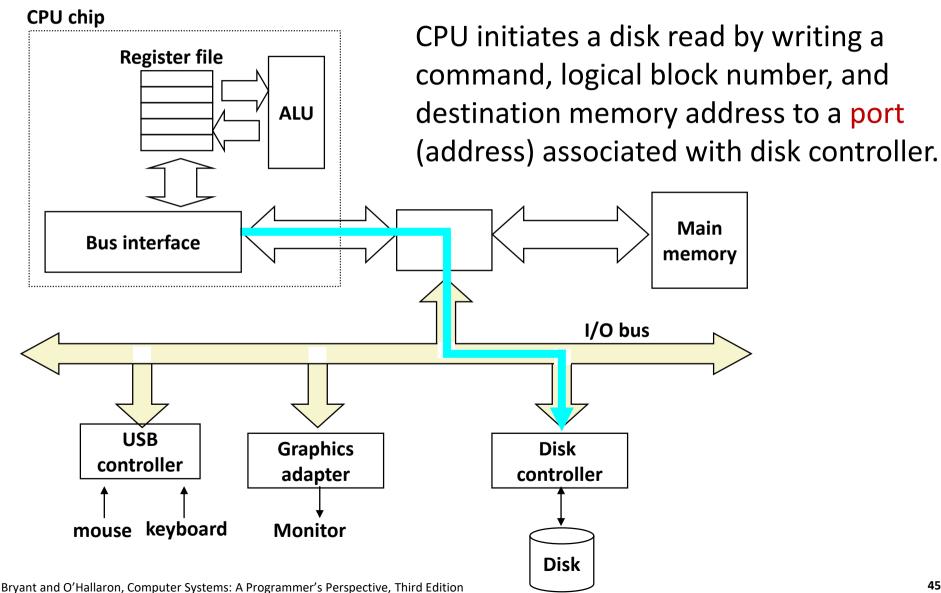
Logical Disk Blocks

- Modern disks present a simpler abstract view of the complex sector geometry:
 - The set of available sectors is modeled as a sequence of b-sized logical blocks (0, 1, 2, ...)
- Mapping between logical blocks and actual (physical) sectors
 - Maintained by hardware/firmware device called disk controller.
 - Converts requests for logical blocks into (surface,track,sector) triples.
- Allows controller to set aside spare cylinders for each zone.
 - Accounts for the difference in "formatted capacity" and "maximum capacity".

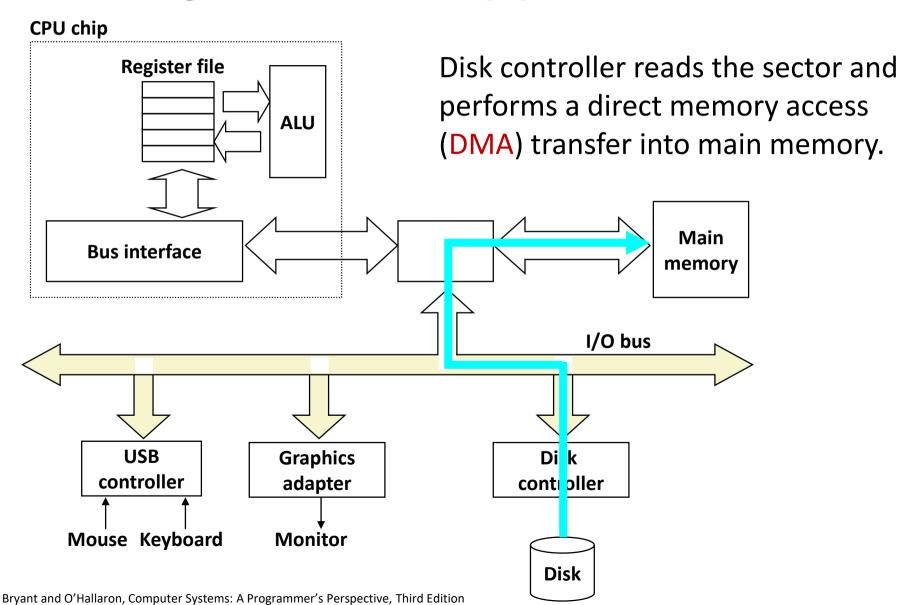
I/O Bus



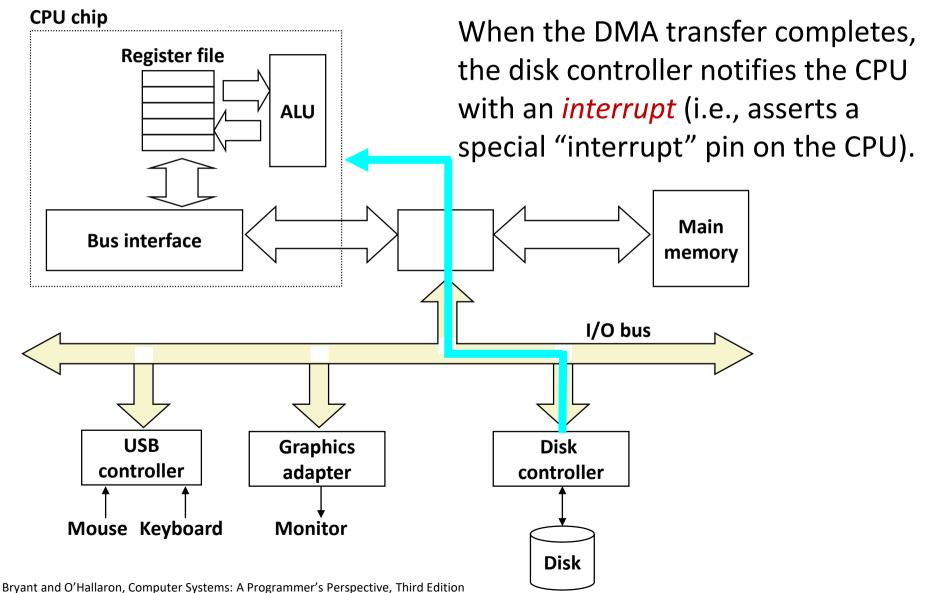
Reading a Disk Sector (1)



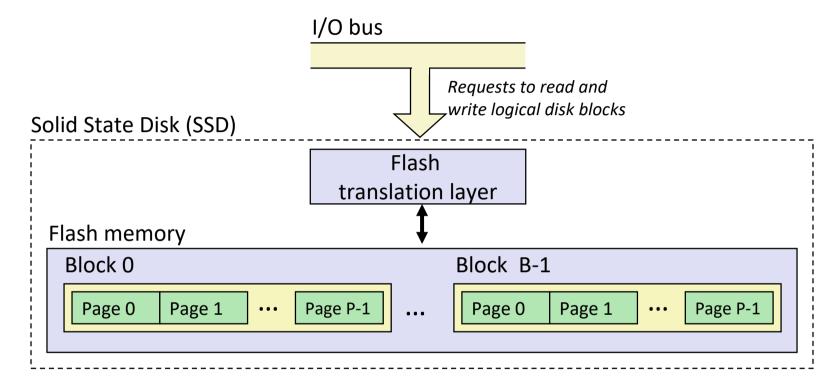
Reading a Disk Sector (2)



Reading a Disk Sector (3)



Solid State Disks (SSDs)



- Pages: 512KB to 4KB, Blocks: 32 to 128 pages
- Data read/written in units of pages.
- Page can be written only after its block has been erased.
- A block wears out after about 100,000 repeated writes.

SSD Performance Characteristics

Sequential read tput550 MB/sSequential write tput470 MB/sRandom read tput365 MB/sRandom write tput303 MB/sAvg seq read time50 usAvg seq write time60 us

Sequential access faster than random access

Common theme in the memory hierarchy

Random writes are somewhat slower

- Erasing a block takes a long time (~1 ms).
- Modifying a block page requires all other pages to be copied to new block.
- In earlier SSDs, the read/write gap was much larger. Fixed by flash translation layer.

Source: Intel SSD 730 product specification.

SSD Tradeoffs vs Rotating Disks

Advantages

No moving parts → faster, less power, more rugged

Disadvantages

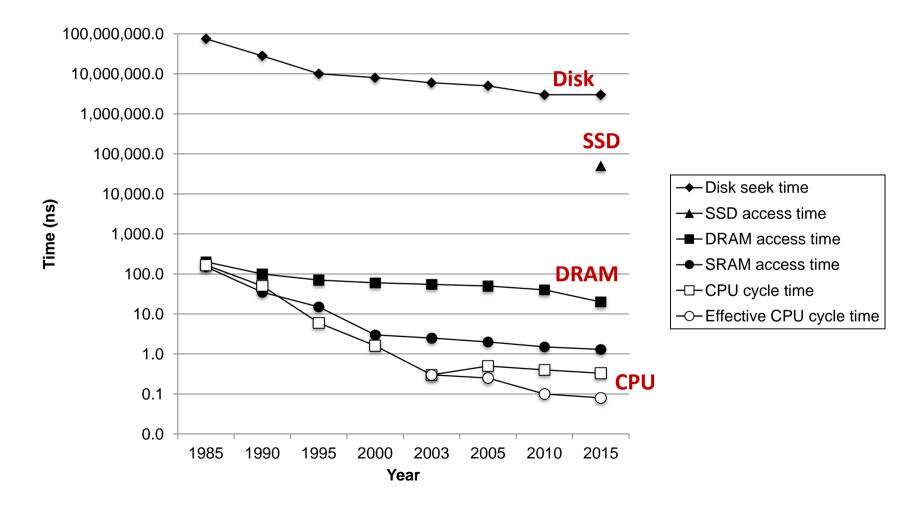
- Have the potential to wear out
 - Mitigated by "wear leveling logic" in flash translation layer
 - E.g. Intel SSD 730 guarantees 128 petabyte (128 x 10¹⁵ bytes) of writes before they wear out
- In 2015, about 30 times more expensive per byte

Applications

- Smart phones, laptops, IoT systems
- Increasingly common in desktops and servers

The CPU-Memory Gap

The gap widens between DRAM, disk, and CPU speeds.



Locality to the Rescue!

The key to bridging this CPU-Memory gap is a fundamental property of computer programs known as locality.

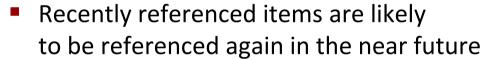
Today

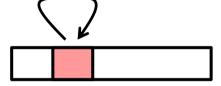
- Storage technologies and trends
- Locality of reference
- Caching in the memory hierarchy

Locality

 Principle of Locality: Programs tend to use data and instructions with addresses near or equal to those they have used recently

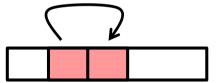








 Items with nearby addresses tend to be referenced close together in time



Locality Example

```
sum = 0;
for (i = 0; i < n; i++)
    sum += a[i];
return sum;</pre>
```

Data references

 Reference array elements in succession (stride-1 reference pattern).

Reference variable sum each iteration.

Instruction references

Reference instructions in sequence.

Cycle through loop repeatedly.

Spatial or Temporal Locality?

spatial

temporal

spatial

temporal

Qualitative Estimates of Locality

- Claim: Being able to look at code and get a qualitative sense of its locality is a key skill for a professional programmer.
- Question: Does this function have good locality with respect to array a?

```
int sum_array_rows(int a[M][N])
{
   int i, j, sum = 0;

   for (i = 0; i < M; i++)
        for (j = 0; j < N; j++)
            sum += a[i][j];
   return sum;
}</pre>
```

Hint: array layout is row-major order

Answer: yes

Locality Example

Question: Does this function have good locality with respect to array a?

```
int sum_array_cols(int a[M][N])
{
   int i, j, sum = 0;

   for (j = 0; j < N; j++)
        for (i = 0; i < M; i++)
            sum += a[i][j];
   return sum;
}</pre>
```

Answer: no, unless...

M is very small

Locality Example

Question: Can you permute the loops so that the function scans the 3-d array a with a stride-1 reference pattern (and thus has good spatial locality)?

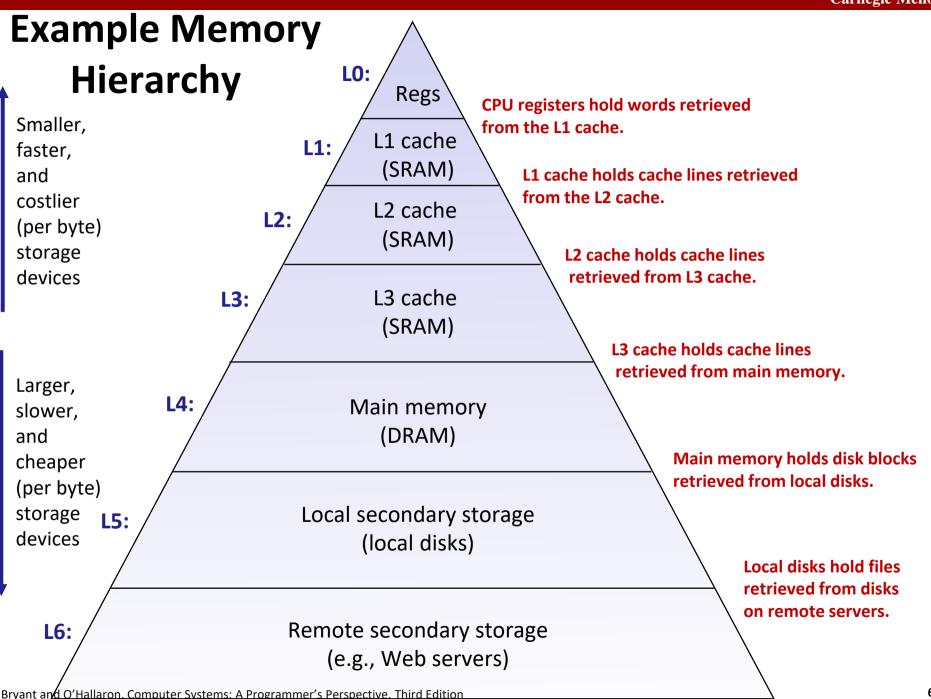
Answer: k outer, i middle, j inner

Memory Hierarchies

- Some fundamental and enduring properties of hardware and software:
 - Fast storage technologies cost more per byte, have less capacity, and require more power (heat!).
 - The gap between CPU and main memory speed is widening.
 - Well-written programs tend to exhibit good locality.
- These fundamental properties complement each other beautifully.
- They suggest an approach for organizing memory and storage systems known as a memory hierarchy.

Today

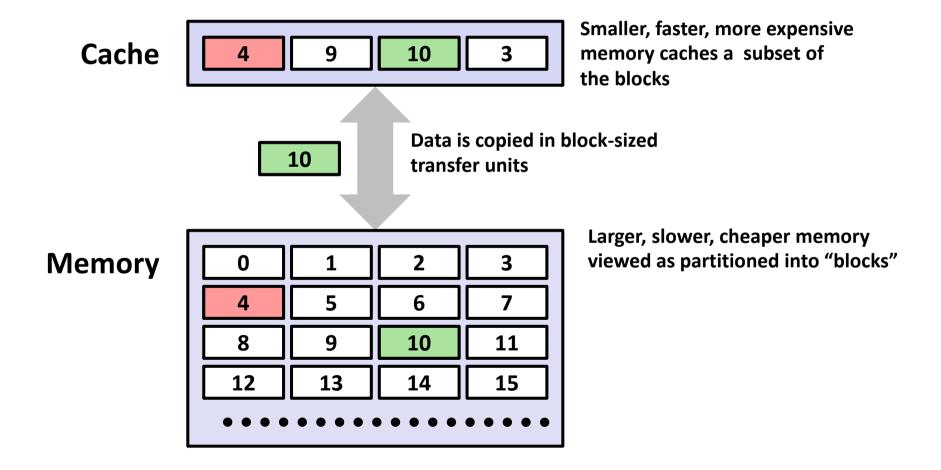
- Storage technologies and trends
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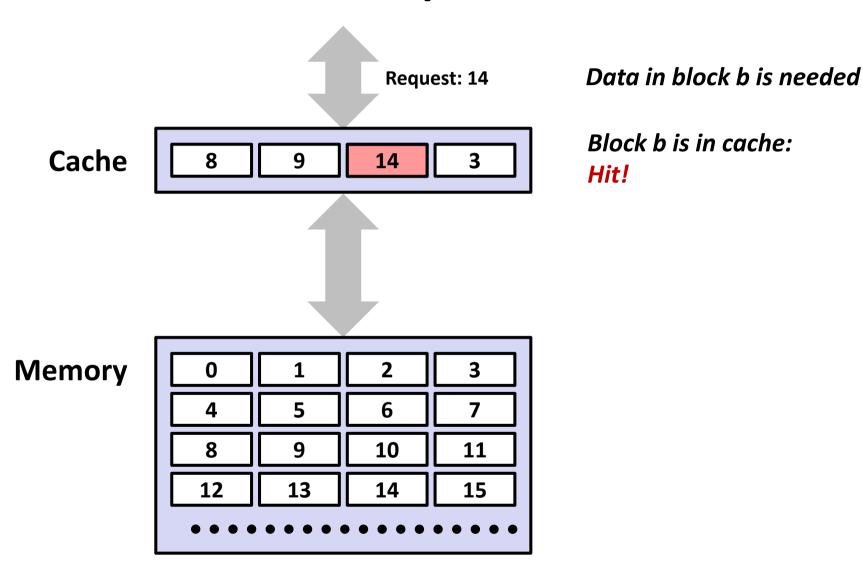
Caches

- Cache: A smaller, faster storage device that acts as a staging area for a subset of the data in a larger, slower device.
- Fundamental idea of a memory hierarchy:
 - For each k, the faster, smaller device at level k serves as a cache for the larger, slower device at level k+1.
- Why do memory hierarchies work?
 - Because of locality, programs tend to access the data at level k more often than they access the data at level k+1.
 - Thus, the storage at level k+1 can be slower, and thus larger and cheaper per bit.
- Big Idea (Ideal): The memory hierarchy creates a large pool of storage that costs as much as the cheap storage near the bottom, but that serves data to programs at the rate of the fast storage near the top.

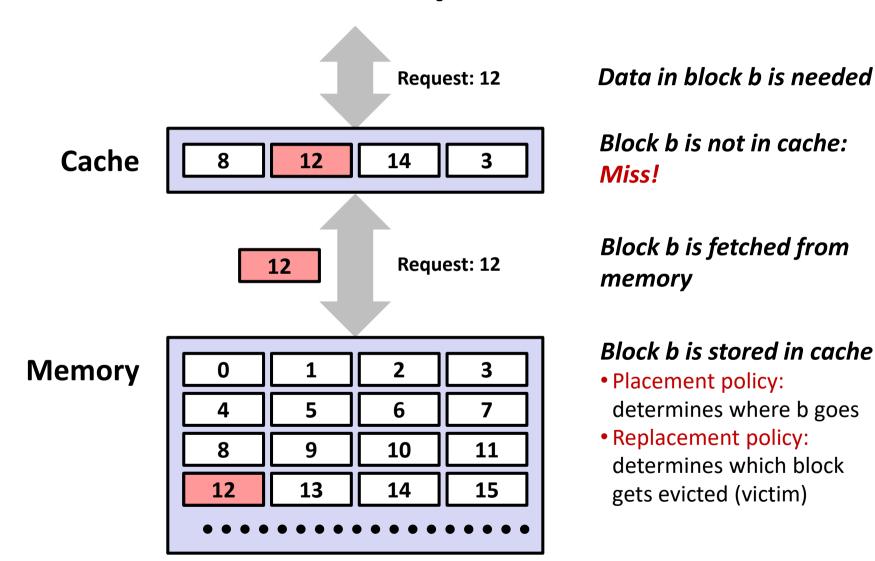
General Cache Concepts



General Cache Concepts: Hit



General Cache Concepts: Miss



General Caching Concepts: 3 Types of Cache Misses

■ Cold (compulsory) miss

 Cold misses occur because the cache starts empty and this is the first reference to the block.

Capacity miss

 Occurs when the set of active cache blocks (working set) is larger than the cache.

Conflict miss

- Most caches limit blocks at level k+1 to a small subset (sometimes a singleton) of the block positions at level k.
 - E.g. Block i at level k+1 must be placed in block (i mod 4) at level k.
- Conflict misses occur when the level k cache is large enough, but multiple data objects all map to the same level k block.
 - E.g. Referencing blocks 0, 8, 0, 8, 0, 8, ... would miss every time.

Examples of Caching in the Mem. Hierarchy

| Cache Type | What is Cached? | Where is it Cached? | Latency (cycles) | Managed By |
|----------------------|----------------------|---------------------|------------------|---------------------|
| Registers | 4-8 bytes words | CPU core | 0 | SW/Compiler |
| TLB | Address translations | On-Chip TLB | 0 | Hardware MMU |
| L1 cache | 64-byte blocks | On-Chip L1 | 4 | Hardware |
| L2 cache | 64-byte blocks | On-Chip L2 | 10 | Hardware |
| Virtual Memory | 4-KB pages | Main memory | 100 | Hardware + OS |
| Buffer cache | Parts of files | Main memory | 100 | os |
| Disk cache | Disk sectors | Disk controller | 100,000 | Disk firmware |
| Network buffer cache | Parts of files | Local disk | 10,000,000 | NFS client |
| Browser cache | Web pages | Local disk | 10,000,000 | Web browser |
| Web cache | Web pages | Remote server disks | 1,000,000,000 | Web proxy server |

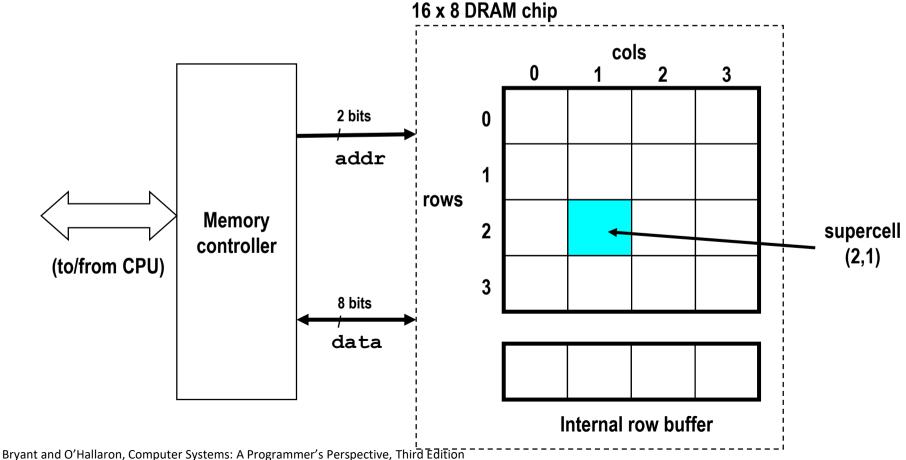
Summary

- The speed gap between CPU, memory and mass storage continues to widen.
- Well-written programs exhibit a property called locality.
- Memory hierarchies based on caching close the gap by exploiting locality.

Conventional DRAM Organization

d x w DRAM:

dw total bits organized as d supercells of size w bits

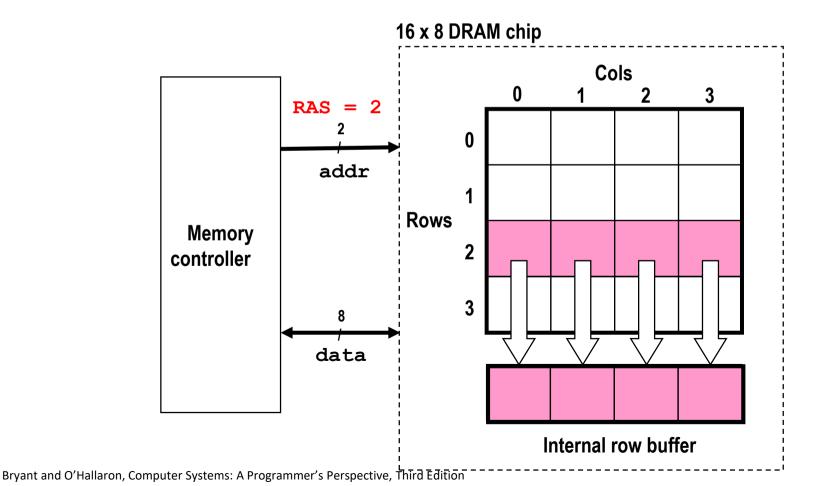


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Reading DRAM Supercell (2,1)

Step 1(a): Row access strobe (RAS) selects row 2.

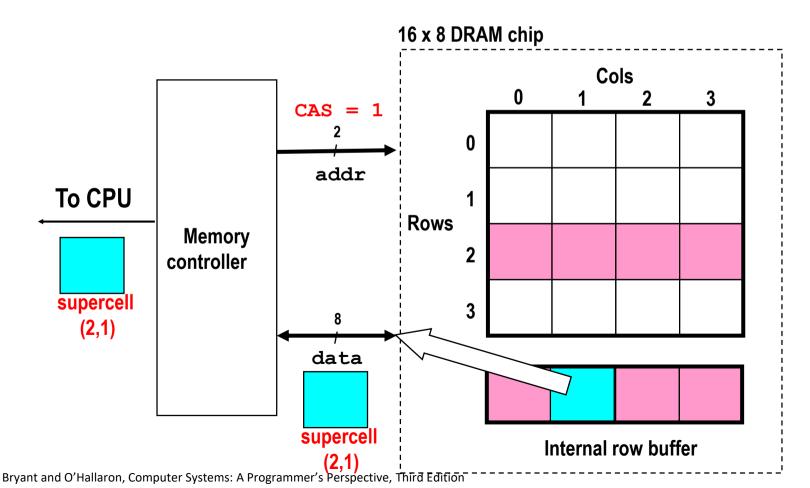
Step 1(b): Row 2 copied from DRAM array to row buffer.



Reading DRAM Supercell (2,1)

Step 2(a): Column access strobe (CAS) selects column 1.

Step 2(b): Supercell (2,1) copied from buffer to data lines, and eventually back to the CPU.



Memory Modules

